AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A liquid crystal device having a thin film transistor, comprising:

a plurality of gate lines formed on a substrate;

a plurality of data lines insulated from and intersecting said gate lines, said data lines and intersecting gate lines defining a plurality of cells, at least one cell including,

a pixel electrode,

a thin film transistor connected to one of the data lines and one of the gate lines defining the cell,

a storage capacitor, and

a metallic pattern, surrounding the cell, including a drain electrode of the thin film transistor and a storage electrode of the storage capacitor in a single layer and being electrically connected to the pixel electrode, wherein [the] said storage electrode is an upper storage electrode of the storage capacitor, and is formed over the one of the gate lines.

2. (Previously Presented) The liquid crystal device of claim 1, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor.

3. (Previously Presented) The liquid crystal device of claim 2, further comprising:

a protective layer disposed between the pixel electrode and the metallic pattern, and wherein

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

4. (Previously Presented) The liquid crystal device of claim 1, further comprising:

a protective layer disposed between the pixel electrode and the metallic pattern, and wherein

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

5. (Previously Presented) The liquid crystal device of claim 4, wherein

the metallic pattern has an annular shape, and

an entire periphery of the pixel electrode overlaps the metallic pattern.

6. (Previously Presented) The liquid crystal device of claim 5, wherein the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor.

7. (Previously Presented) The substrate of claim 1, further comprising:

a protective layer disposed between the pixel electrode and the metallic pattern, and wherein

the pixel electrode is connected to a storage electrode part of the metallic pattern via a first contact hole in the protective layer.

8. (Previously Presented) The liquid crystal device of claim 7, wherein the protective layer does not include a contact hole over a drain electrode part of the metallic pattern.

9. (Previously Presented) The liquid crystal device of claim 8, wherein the drain electrode part has a greater area than a drain electrode part electrically connected to the pixel electrode via a contact hole in the protective layer over the drain electrode part.

10. (Previously Presented) The liquid crystal device of claim 8, wherein the pixel electrode has a larger aspect ratio than if the drain electrode part was electrically connected to the pixel electrode via a contact hole in the protective layer over the drain electrode part.

11. (Previously Presented) The liquid crystal device of claim 8, wherein

the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

12. (Previously Presented) The liquid crystal device of claim 8, wherein

the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

13. (Previously Presented) The liquid crystal device of claim 7, wherein

the pixel electrode is connected to a drain electrode part of the metallic pattern via a second contact hole in the protective layer.

14. (Previously Presented) The liquid crystal device of claim 13, wherein

the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

15. (Previously Presented) The liquid crystal device of claim 13, wherein

the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

16. (Previously Presented) The liquid crystal device of claim 1, further comprising:

a protective layer disposed between the pixel electrode and the metallic pattern, and wherein

the pixel electrode is connected to a drain electrode part of the metallic pattern via a contact hole in the protective layer.

17. (Previously Presented) The liquid crystal device of claim 16, wherein the protective layer does not include a contact hole over a storage electrode part of the metallic pattern.

18. (Previously Presented) The liquid crystal device of claim 17, wherein the pixel electrode overlaps a gate line, defining the cell but not connected to the thin film transistor, the overlap of the gate line being less than an overlap in a case wherein the protective layer includes a contact hole over a storage electrode part of the metallic pattern.

19. (Previously Presented) The liquid crystal device of claim 17, wherein

the metallic pattern is spaced a predetermined distance from the data line connected to the thin film transistor; and

a portion of a periphery of the pixel electrode overlaps the metallic pattern.

20. (Previously Presented) The liquid crystal device of claim 16, wherein

the metallic pattern has an annular shape and is spaced a predetermined distance from the data line connected to the thin film transistor; and

an entire periphery of the pixel electrode overlaps the metallic pattern.

21. (Currently Amended) A liquid crystal device having a thin film transistor, comprising:

a plurality of gate lines formed on a substrate;

a plurality of data lines insulated from and intersecting said gate lines, said data lines and intersecting gate lines defining a plurality of cells, at least one cell including,

a pixel electrode,

a thin film transistor interposed between one of the data lines and the pixel electrode and including a source electrode connected to the one of the data lines, a gate electrode connected to one of the gate lines, a drain electrode, and

a storage capacitor, surrounding the cell, including a storage electrode and a drain electrode in a single layer, the storage capacitor being connected to the pixel electrode, wherein [the] said storage electrode is an upper storage electrode of the storage capacitor and is formed over the one of the gate lines.

22. (Previously Presented) The liquid crystal device of claim 21, wherein the storage electrode and the drain electrode are connected to each other by a metallic pattern.

23. (Currently Amended) A method of manufacturing a thin film transistor substrate, comprising:

forming a gate line having a gate electrode on a transparent substrate;

forming a gate insulating layer on the gate electrode;

forming a semiconductor layer on the gate insulating layer;

simultaneously forming a data line having a source electrode, and a metallic pattern including a drain electrode part and a storage electrode part in a single layer, wherein the storage electrode part is an upper storage electrode of a storage capacitor and is formed over the gate line;

forming a protective film over the entire surface; and

forming a pixel electrode over the protective film.

24. (Previously Presented) The method of claim 23, wherein the forming the data line and the metallic pattern step is performed simultaneously by forming a conductive layer over the substrate and patterning the conductive layer to form the data line and the metallic pattern such that the metallic pattern is spaced a predetermined distance from the data line.

25. (Original) The method of claim 23, wherein the forming a pixel electrode step forms the pixel electrode such that a portion of a periphery of the pixel electrode overlaps the metallic pattern.

26. (Original) The method of claim 23, wherein the forming a pixel electrode step forms the pixel electrode such that an entire periphery of the pixel electrode overlaps the metallic pattern.

27. (Previously Presented) The method of claim 23, wherein the forming a protective layer step forms the protective layer with a first contact hole exposing the storage electrode part of the metallic pattern.

28. (Original) The method of claim 27, wherein the forming a protective layer step does not form the protective layer with a contact hole exposing the drain electrode part of the metallic pattern.

29. (Original) The method of claim 27, wherein the forming a protective layer step forms the protective layer with a second contact hole exposing the drain electrode part of the metallic pattern.

30. (Original) The method of claim 23, wherein the forming a protective layer step forms the protective layer with a contact hole exposing the drain electrode part of the metallic pattern.

31. (Previously Presented) The method of claim 30, wherein the forming a protective layer step does not form the protective layer with a contact hole exposing the storage electrode part of the metallic pattern.